

Ultrafast, Soft Recovery Diode

- Ultra fast Recovery
- · Ultra soft Recovery
- Very Low IRRM
- Very Low Qrr
- · Specified at Operating Conditions
- Lead-Free

V _R	600	٧
$V_{F(Max)}$	1.7	>
Qrr	65	nC
D _{I (rec)M/} dt	240	A /µs



Benefits

- · Reduced RFI and EMI
- Reduced Power Loss in Diode and Switching Transistor
- · Higher Frequency Operation
- Reduced Snubbing
- · Reduced Parts Count

Description

International Rectifier's HFA08TB60PbF is a state of the art ultra fast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 600 volts and 8 amps per Leg continuous current, the HFA08TB60PbF is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultra fast recovery time, the ultra fast recovery diode product line features extremely low values of peak recovery current (IRRM) and does not exhibit any tendency to "snap-off" during the tb portion of recovery. The ultra fast recovery diode features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These ultra fast recovery diode advantages can help to significantly reduce snubbing, component count and heat sink sizes. The HFA08TB60PbF is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

		Standard Pack			
Base part number	Package Type	Form	Quantity	Orderable Part Number	
HFA08TB60PbF	TO-220AC	Tube	50	HFA08TB60PbF	

Absolute Maximum Ratings

	Parameter	Max.	Units	
V_R	Cathode -to – Anode Voltage	600	V	
I _F @ T _C = 100°C	Continuous Forward Current	8.0		
I _{FSM} Single Pulse Forward Current		60	Α	
I _{FRM} Maximum Repetitive Forward Current		24		
P _D @T _C = 25°C Maximum Power Dissipation		36	10/	
P _D @T _C = 100°C Maximum Power Dissipation		14	W	
T _J Operating Junction and		55 to 1.450	°C	
T _{STG}	Storage Temperature Range	-55 to + 150		



Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
V_{BR}	Cathode Anode Breakdown Voltage	600				I _R = 100μA
			1.4	1.7	V	I _F = 8.0A See Fig. 1
V_{FM}	Max Forward Voltage		1.7	2.1	ľ	I _F = 16A
			1.4	1.7		$I_F = 8.0A$, $T_J = 125^{\circ}C$
	May Payaraa Laakaga Current		0.3	5.0		$V_R = V_R$ Rated See Fig. 2
I _{RM}	Max Reverse Leakage Current		100	500	μA	$T_J = 125^{\circ}C$, $V_R = 0.8 \times V_R$ Rated
C_T	Junction Capacitance		10	25	pF	$V_R = 200V$ See Fig. 3
Ls	Series Inductance		8.0		ı nH	Measured lead to lead 5mm from package body

Dynamic Recovery Characteristics @ TJ = 25°C (unless otherwise specified)

	Parameter	Min.	Тур.	Max.	Units	Conditions
trr			18			$I_F = 1.0A$, dif/dt = 200A/ μ s, $V_R = 30V$
trr1	Reverse Recovery Time See Fig. 5		37	55	ns	T _J = 25°C
trr2	55		90		T _J = 125°C	
I _{RRM1}	Peak Recovery Current See Fig. 6		3.5	5.0	Α	$T_J = 25^{\circ}C$ $I_F = 8.0A$
I _{RRM2}	l eak Necovery Current See Fig. 0		4.5	8.0 A		$T_J = 125^{\circ}C$ $V_R = 200V$
Q _{rr1}	Davierra Dagaver / Charge Cap Fig 7		65	138		$T_J = 25^{\circ}C$ di/dt = 200A/µs
Q _{rr2}	Reverse Recovery Charge See Fig.7		124	360	nC	T _J = 125°C
di _{(rec)M/} dt1	Peak Rate of Fall of Recovery Current		240		Α /:	T _J = 25°C
di _{(rec)M/} dt2	During tb See Fig.8		210		A/µs	T _J = 125°C

Thermal Resistance

	Parameter	Min.	Тур.	Max.	Units
T _{lead} ①	Lead Temperature			300	
$R_{\theta JC}$	Thermal Resistance, Junction to Case			3.5	
R _{0JA} ②	Thermal Resistance, Junction to Ambient			62	°C/W
$R_{\theta CS}$ ③			0.50		
14/4	Mainh		2.0		g
Wt	Weight		0.07		(oz)
т	Mounting Torque	6.0		12	Kg-cm
1	Mounting Torque	5.0		10	lbf•in

- ① 0.063 in. from Case (1.6mm) for 10 sec
- ② Typical Socket Mount
- 3 Mounting Surface, Flat, Smooth and Greased



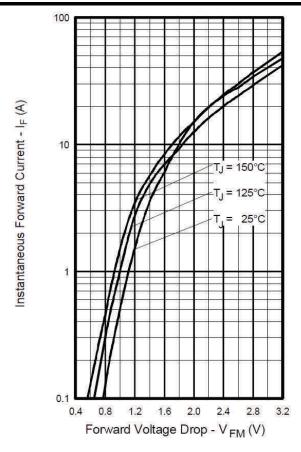


Fig. 1 - Maximum Forward Voltage Drop vs. Instantaneous Forward Current

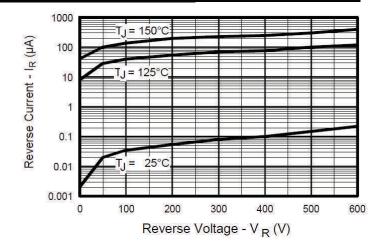


Fig. 2 - Typical Reverse Current vs. Reverse Voltage

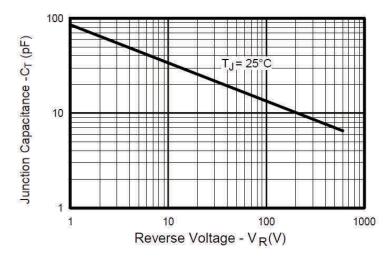


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

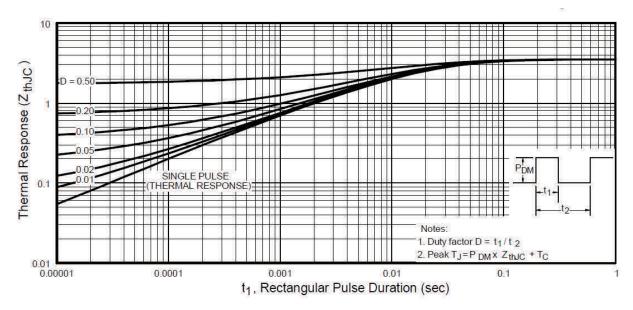
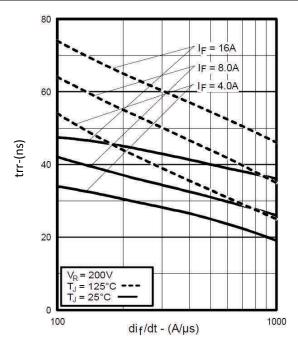


Fig. 4 - Maximum Thermal Impedance Zthjc Characteristics





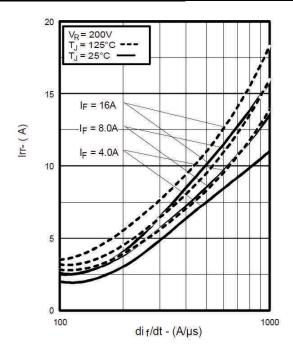
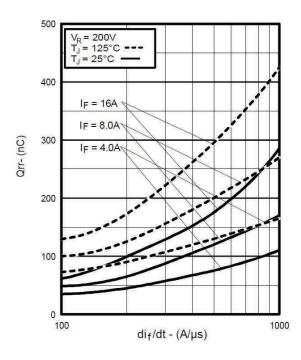


Fig. 5 - Typical Reverse Recovery vs. dif/dt

Fig. 6 - Typical Recovery Current vs. dif/dt

10000



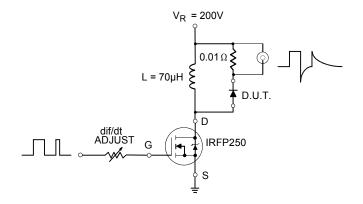
V_R = 200V T_J = 125°C T_J = 25°C I_F = 16A I_F = 8.0A I_F = 4.0A I_G = 4.0A I_G = 4.0A I_G = 4.0A

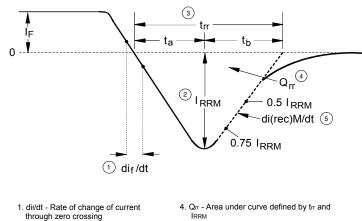
Fig. 7 - Typical Stored Charge vs. dif/dt

Fig. 8 - Typical di(rec)M/dt vs. dif/dt



REVERSE RECOVERY CIRCUIT





- through zero crossing
 2. IRRM Peak reverse recovery current
- Irr. Reverse recovery current
 Irr. Reverse recovery time measured
 from zero crossing point of negative
 going IF to point where a line passing
 through 0.75 IrRM and 0.50 IRRM
 extrapolated to zero current
- trr X IRRM

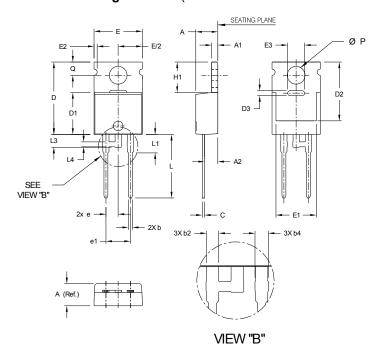
5. di(rec)M/dt - Peak rate of change of current during to portion of trr

Fig. 9 - Reverse Recovery Parameter Test Circuit

Fig. 10 - Reverse Recovery Waveform and Definitions



TO-220AC Package Outline (Dimensions are shown in millimeters (inches))

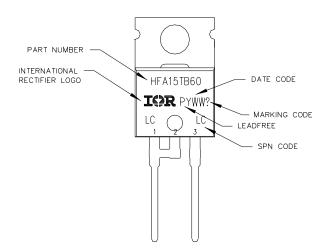


SYMBOL	MIN.	NOM.	MAX.		
А	3.56	4.57	4.83		
A1	1.14	1.27	1.40		
A2	2.03	2.77	2.92		
b	0.38	0.81	1.01		
b2	1.17	1.27	1.37		
b4	1.25	1.35	1.45		
С	0.36	0.46	0.61		
D	14.32	15.00	16.51		
D1	8.38	8.69	9.02		
D2	11.68	12.19	12.88		
D3	0.82	1.02	1.22		
E	9.65	10.00	10.67		
E1	6.86	8.39	8.89		
E2	1		0.76		
E3	3.30	3.50	3.70		
е	2	2.54 BASI	0		
e1	5.08 BASIC				
H1	5.84	6.31	6.86		
L	12.70	13.16	14.73		
L1	3.56	3.83	4.06		
L3	2.31	2.56	2.81		
L4	0.76	1.01	1.27		
ØΡ	3.54	3.68	4.08		
Q	2.54	2.74	3.42		

NOTES:

- 1. DIMENSIONING AND TOLERANCING AS PER ASME Y14.5M 1994.
- 2. DIMENSIONS ARE SHOWN IN MILLIMETERS.

TO-220AC Part Marking Information



Note: For the most current drawing please refer to IR website at http://www.irf.com/package/



Qualification Information[†]

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Qualification I avai	Industrial					
Qualification Level	(per JEDEC JESD47F) ††					
Moisture Sensitivity Level	TO-220AC N/A					
RoHS Compliant	Yes					

- † Qualification standards can be found at International Rectifier's web site: http://www.irf.com/product-info/reliability/
- †† Applicable version of JEDEC standard at the time of product release.



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To contact International Rectifier, please visit http://www.irf.com/whoto-call/

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